

2SK2340

Silicon N-Channel Power F-MOS FET

■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

■ Applications

- Contactless relay
- Driving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

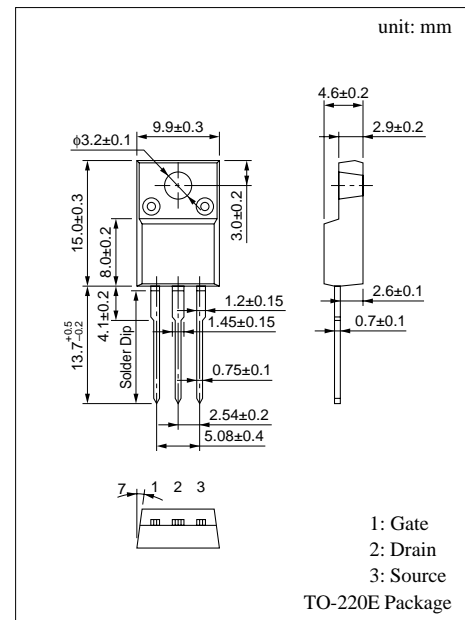
■ Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit	
Drain to Source breakdown voltage	V_{DSS}	900	V	
Gate to Source voltage	V_{GSS}	± 30	V	
Drain current	DC	I_D	± 5	A
	Pulse	I_{DP}	± 10	A
Avalanche energy capacity	EAS*	45	mJ	
Allowable power dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_a = 25^\circ\text{C}$		2	
Channel temperature	T_{ch}	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

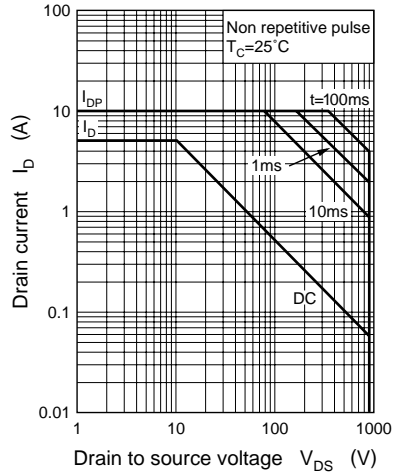
* $L = 3.6\text{mH}$, $I_L = 5\text{A}$, 1 pulse

■ Electrical Characteristics ($T_C = 25^\circ\text{C}$)

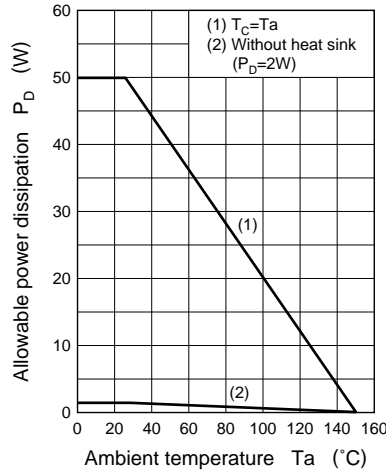
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 720\text{V}$, $V_{GS} = 0$			100	μA	
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0$			± 1	μA	
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	900			V	
Gate threshold voltage	V_{th}	$V_{DS} = 25\text{V}$, $I_D = 1\text{mA}$	2		5	V	
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$		2	2.8	Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25\text{V}$, $I_D = 3\text{A}$	1.5	3.5		S	
Diode forward voltage	V_{DSF}	$I_{DR} = 5\text{A}$, $V_{GS} = 0$			-1.6	V	
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 20\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		1400		pF	
Output capacitance (Common Source)	C_{oss}				140		pF
Reverse transfer capacitance (Common Source)	C_{rss}				60		pF
Turn-on time (delay time)	$t_{d(on)}$				30		ns
Rise time	t_r	$V_{DD} = 200\text{V}$, $I_D = 3\text{A}$ $V_{GS} = 10\text{V}$, $R_L = 66.6\Omega$		60		ns	
Fall time	t_f				60		ns
Turn-off time (delay time)	$t_{d(off)}$				170		ns
Thermal resistance between channel and case	$R_{th(ch-c)}$				2.5	$^\circ\text{C/W}$	
Thermal resistance between channel and atmosphere	$R_{th(ch-a)}$				62.5	$^\circ\text{C/W}$	



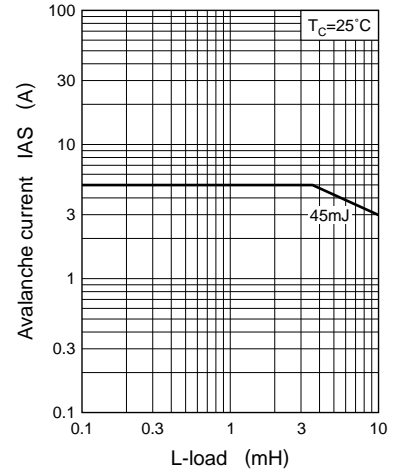
Area of safe operation (ASO)



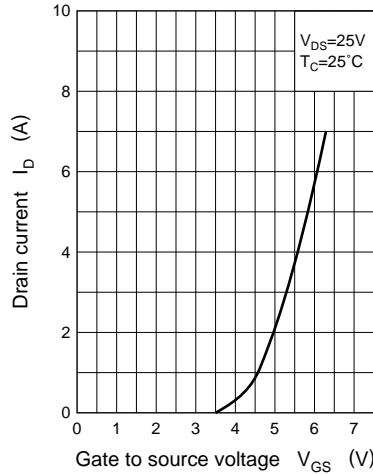
P_D — T_a



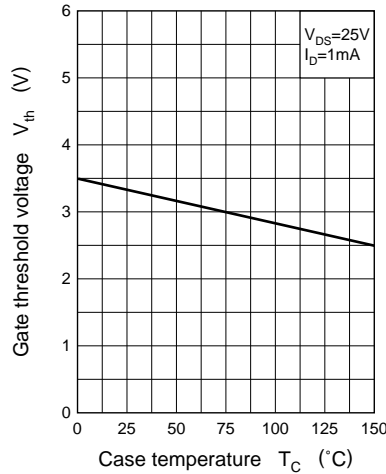
IAS — L-load



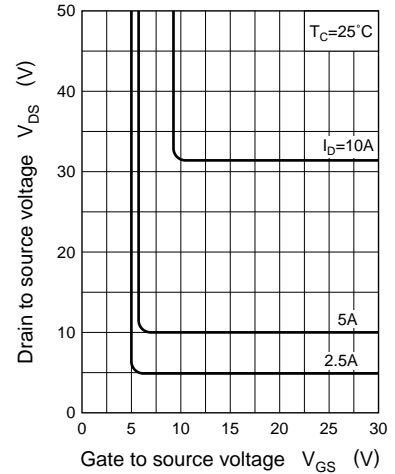
I_D — V_{GS}



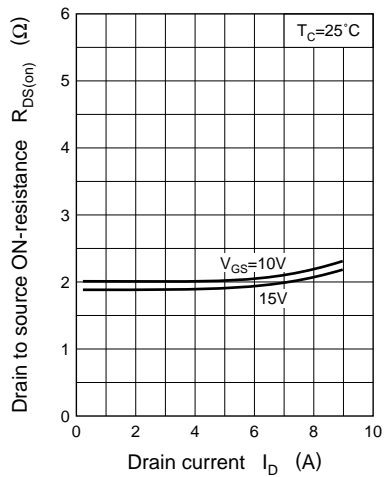
V_{th} — T_C



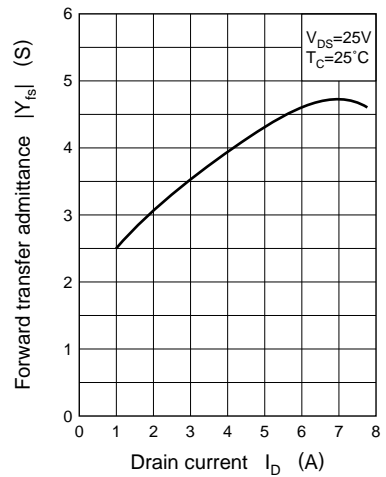
V_{DS} — V_{GS}



$R_{DS(on)}$ — I_D



$|Y_{fs}|$ — I_D



$C_{iss}, C_{oss}, C_{rss}$ — V_{DS}

